


REMARKS

In response to the Examiner's Restriction Requirement dated June 25, 2004, Applicants hereby elect Group C, claims 35-40, directed to a method of forming a semiconductor device wherein a silicon oxide layer is formed on the surface of the interconnection groove is formed following the formation of a resist layer inside the groove then subsequently removed after the removal of the resist film formed on the surface of the substrate, as shown in embodiment of Figure 5 for prosecution on the merits in the present application. As a result, claims 1-34 are cancelled herein.

In view of the above, examination of the elected invention on the merits is hereby earnestly solicited.

Should the Examiner believe a conference would be of benefit in expediting the prosecution of the instant application, he is hereby invited to telephone counsel to arrange such a conference.

Respectfully submitted,



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